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Product: SMD1812P200TFT

Revision: B

Date: January 08, 2010

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Device Specification

ELECTRICAL CHARACTERISTICS



Part Number						Maximum Time To Trip		Resistance	
	I _{hold} (A)	I _{trip} (A)	V _{max} (Vdc)	I _{max} (A)	P _{d typ} (W)	Current (A)	Time (Sec.)	$R_{min} \ (\Omega)$	R_{1max} (Ω)
SMD1812P200TFT	2.00	3.50	8	100	0.80	8.00	2.00	0.020	0.070

Note: Ihold = Hold current: maximum current device will pass without tripping in 23°C still air.

l_{trip} = Trip current: minimum current at which the device will trip in 23°C still air.

V_{max} = Maximum voltage device can withstand without damage at rated current (I_{max})

 I_{max} = Maximum fault current device can withstand without damage at rated voltage (V_{max})

 $P_{d\,typ}\,$ = Typical power dissipated from device when in the tripped state at 23 °C still air.

R_{min} = Minimum resistance of device in initial (un-soldered) state.

R_{1max} = Maximum resistance of device at 23°C measured one hour after tripping or reflow soldering of 260°C for 20 sec.

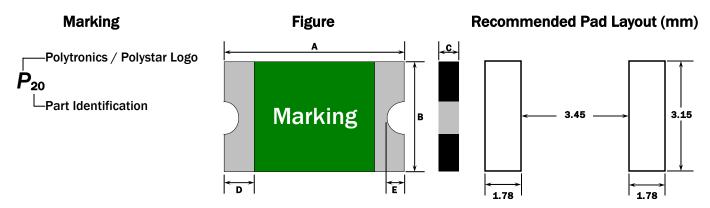
*Value specified were determined using the PWB with 0.030"*1.5oz copper traces.

*Customer should verify the device performance in their specified conditions.

Caution: Operation beyond the specified rating may result in damage and possible arcing and flame.

Recognitions:





Note: Polystar is Polytronics's manufacturing site in China. The Polystar ID marking shall appear on smallest package.

PHYSICAL DIMENSIONS (mm)

Part Number	Α		В		С		D		Е	
	Min.	Max.								
SMD1812P200TFT	4.37	4.73	3.07	3.41	0.20	0.60	0.30	1.20	0.15	0.65

Specifications are subject to change without notice.

单击下面可查看定价,库存,交付和生命周期等信息

☆聚点